

## **Bi-directional 5V LOW Capacitance ESD Protector**

### **Description**

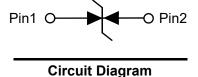
The PESDUC2FD5VBN protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



DFN1006-2L(Bottom View)

#### **Feature**

- $\triangleright$  80W peak pulse power per line (t<sub>p</sub> = 8/20µs)
- ➤ DFN1006-2L package
- Response time is typically < 1 ns</p>
- > Bidirectional configurations
- ➤ Low clamping voltage
- > RoHS compliant
- ➤ Transient protection for data lines to IEC 61000-4-2(ESD) ±25kV(air), ± 25kV(contact); IEC 61000-4-5 (Lightning) 4A (8/20us)





#### **Applications**

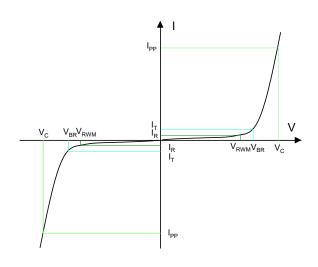
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- ➤ Portable instrumentation
- Cordless phones
- Digital cameras
- > Peripherals

#### **Mechanical Characteristics**

- Mounting position: Any
- ➤ Qualified max reflow temperature:260°C
- > Device meets MSL 1 requirements
- > DFN1006-2L without plating

## **Electronics Parameter**

Symbol	Parameter		
$V_{RWM}$	Peak Reverse Working Voltage		
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>		
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>		
I <sub>T</sub>	Test Current		
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current		
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>		
P <sub>PP</sub>	Peak Pulse Power		
CJ	C <sub>J</sub> Junction Capacitance		
I <sub>F</sub>	Forward Current		
$V_{F}$	Forward Voltage @ I <sub>F</sub>		



# Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	$V_{RWM}$	-	-	-	5.0	V
Breakdown Voltage	$V_{BR}$	I <sub>t</sub> = 1mA	5.6	-	9.0	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 5V	-	-	100	nA
Clamping Voltage	V <sub>C</sub>	$I_{PP} = 4A, t_P = 8/20 \mu s$	-	-	21	V
Junction Capacitance	CJ	$V_R = 0V, f = 1MHz$	-	0.25	0.5	pF

# Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>P</sub> = 8/20µs )	P <sub>PP</sub>	80	W
Peak Pulse Current ( t <sub>P</sub> = 8/20μs )	I <sub>PP</sub>	4.0	А
Lead Soldering Temperature	T <sub>L</sub>	260 (10 sec)	°C
Junction and Storage Temperature Range	$T_{J,}T_{STG}$	-55~+150	°C
ESD Protection-Contact Discharge	V <sub>ESD</sub>	±25	kV
ESD Protection-Air Discharge	V <sub>ESD</sub>	±25	kV

# Typical Characteristics

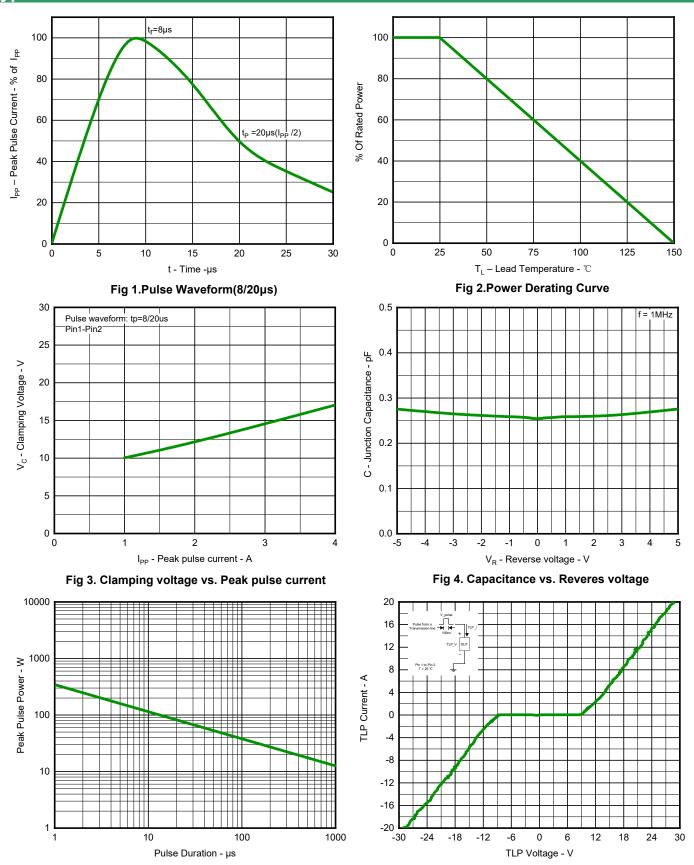
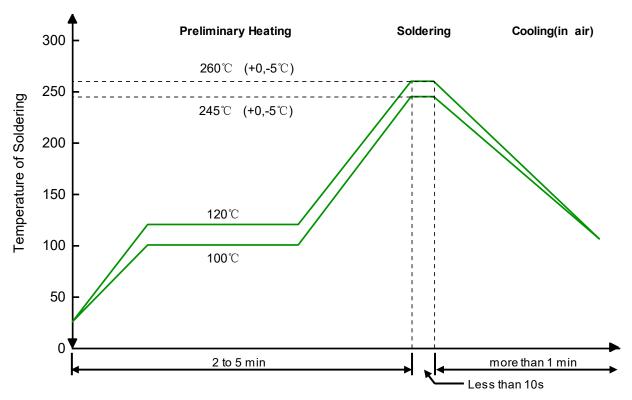


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

Fig 6. TLP Measurement

## **Solder Reflow Recommendation**



Remark: Pb free for 260°C; Pb for 245°C.

### **PCB** Design

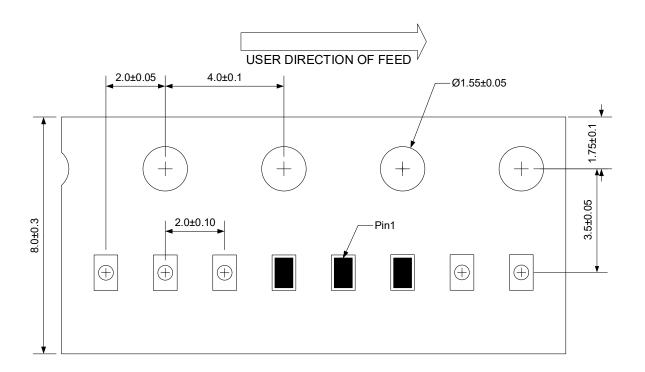
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

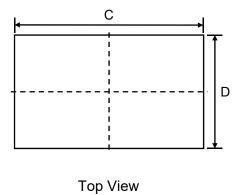
### **Ordering information**

Device	Package	Reel	Shipping
PESDUC2FD5VBN	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

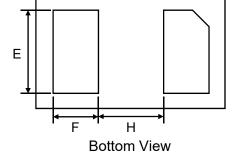
### Load with information

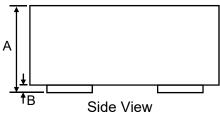


## Product dimension (DFN1006-2L)



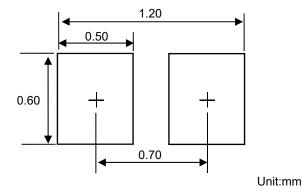
Di





			ŤB	S	ide View
m	Millimeters		Inches		
	Min	Max	Min	Max	
٩	0.40	0.55	0.016	0.022	
3	0.00	0.05	0.000	0.002	

	141111	IVIAA	141111	IVIAA
Α	0.40	0.55	0.016	0.022
В	0.00	0.05	0.000	0.002
С	0.90	1.10	0.035	0.043
D	0.55	0.65	0.022	0.026
Е	0.35	0.55	0.014	0.022
F	0.15	0.30	0.006	0.012
Н	0.40 Тур.		0.015	5 Тур.



Suggested PCB Layout

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